# MC33272A, MC33274A, NCV33274A

# Operational Amplifiers, Single Supply, High Slew Rate, Low Input Offset Voltage

The MC33272/74 series of monolithic operational amplifiers are quality fabricated with innovative Bipolar design concepts. This dual and quad operational amplifier series incorporates Bipolar inputs along with a patented Zip–R–Trim element for input offset voltage reduction. The MC33272/74 series of operational amplifiers exhibits low input offset voltage and high gain bandwidth product. Dual –doublet frequency compensation is used to increase the slew rate while maintaining low input noise characteristics. Its all NPN output stage exhibits no deadband crossover distortion, large output voltage swing, and an excellent phase and gain margin. It also provides a low open loop high frequency output impedance with symmetrical source and sink AC frequency performance.

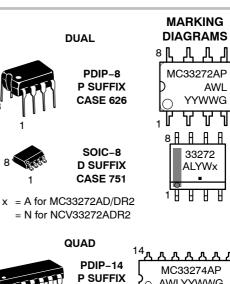
#### **Features**

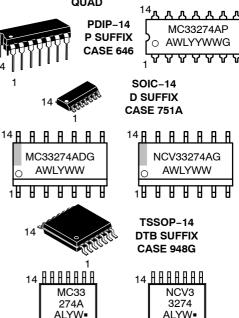
- Input Offset Voltage Trimmed to 100 μV (Typ)
- Low Input Bias Current: 300 nALow Input Offset Current: 3.0 nA
- High Input Resistance: 16 MΩ
- Low Noise:  $18 \text{ nV}/\sqrt{\text{Hz}}$  @ 1.0 kHz
- High Gain Bandwidth Product: 24 MHz @ 100 kHz
- High Slew Rate: 10 V/us
- Power Bandwidth: 160 kHz
- Excellent Frequency Stability
- Unity Gain Stable: w/Capacitance Loads to 500 pF
- Large Output Voltage Swing: +14.1 V/ -14.6 V
- Low Total Harmonic Distortion: 0.003%
- Power Supply Drain Current: 2.15 mA per Amplifier
- Single or Split Supply Operation: +3.0 V to +36 V or ±1.5 V to ±18 V
- ESD Diodes Provide Added Protection to the Inputs
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- Pb-Free Packages are Available

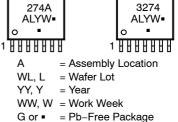


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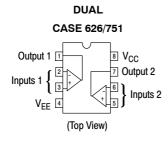


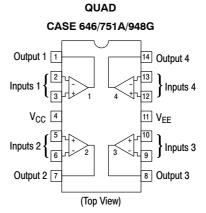
#### **ORDERING INFORMATION**

(Note: Microdot may be in either location)

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

#### **PIN CONNECTIONS**





#### **MAXIMUM RATINGS**

Rating		Symbol	Value	Unit
Supply Voltage		V <sub>CC</sub> to V <sub>EE</sub>	+36	V
Input Differential Voltage Range		$V_{IDR}$	Note 1	V
Input Voltage Range		V <sub>IR</sub>	Note 1	V
Output Short Circuit Duration (Note 2)		t <sub>SC</sub>	Indefinite	sec
Maximum Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>stg</sub>	-60 to +150	°C
ESD Protection at Any Pin	- Human Body Model - Machine Model	V <sub>esd</sub>	2000 200	V
Maximum Power Dissipation		P <sub>D</sub>	Note 2	mW
Operating Temperature Range	MC33272A, MC33274A NCV33272A, NCV33274A	T <sub>A</sub>	-40 to +85 -40 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Either or both input voltages should not exceed V<sub>CC</sub> or V<sub>EE</sub>.
   Power dissipation must be considered to ensure maximum junction temperature (T<sub>J</sub>) is not exceeded (see Figure 2).

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +15 V,  $V_{EE}$  = -15 V,  $T_A$  = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Тур	Max	Unit
Input Offset Voltage ( $R_S = 10 \Omega$ , $V_{CM} = 0 V$ , $V_O = 0 V$ ) ( $V_{CC} = +15 V$ , $V_{EE} = -15 V$ ) $T_A = +25^{\circ}C$ $T_A = -40^{\circ} \text{ to } +85^{\circ}C$ $T_A = -40^{\circ} \text{ to } +125^{\circ}C \text{ (NCV33272A)}$ $T_A = -40^{\circ} \text{ to } +125^{\circ}C \text{ (NCV33274A)}$ ( $V_{CC} = 5.0 V$ , $V_{EE} = 0$ )	3	V <sub>IO</sub>	- - - -	0.1 - - -	1.0 1.8 2.5 3.5	mV
$T_A = +25^{\circ}C$			-	_	2.0	
Average Temperature Coefficient of Input Offset Voltage $R_S = 10 \ \Omega$ , $V_{CM} = 0 \ V$ , $V_O = 0 \ V$ , $T_A = -40^\circ$ to $+125^\circ C$	3	ΔV <sub>IO</sub> /ΔΤ	_	2.0	_	μV/°C
Input Bias Current ( $V_{CM} = 0 \text{ V}, V_O = 0 \text{ V}$ ) $T_A = +25^{\circ}C$ $T_A = T_{low} \text{ to } T_{high}$	4, 5	I <sub>IB</sub>	- -	300 -	650 800	nA
Input Offset Current ( $V_{CM} = 0 \text{ V}, V_O = 0 \text{ V}$ ) $T_A = +25^{\circ}C$ $T_A = T_{low} \text{ to } T_{high}$		lliol	- -	3.0	65 80	nA
Common Mode Input Voltage Range ( $\Delta V_{IO}$ = 5.0 mV, $V_{O}$ = 0 V) $T_{A}$ = +25°C	6	V <sub>ICR</sub>	V <sub>EE</sub>	to (V <sub>CC</sub> -	1.8)	V
Large Signal Voltage Gain ( $V_O$ = 0 V to 10 V, $R_L$ = 2.0 k $\Omega$ ) $T_A = +25^{\circ}C$ $T_A = T_{low} \text{ to } T_{high}$	7	A <sub>VOL</sub>	90 86	100 -		dB
Output Voltage Swing ( $V_{ID}$ = $\pm 1.0$ V) ( $V_{CC}$ = $+15$ V, $V_{EE}$ = $-15$ V) $R_L$ = $2.0$ k $\Omega$ $R_L$ = $2.0$ k $\Omega$ $R_L$ = $10$ k $\Omega$ $R_L$ = $10$ k $\Omega$ ( $V_{CC}$ = $5.0$ V, $V_{EE}$ = $0$ V) $R_L$ = $2.0$ k $\Omega$ $R_L$ = $2.0$ k $\Omega$	8, 9, 12 10, 11	V <sub>O</sub> + V <sub>O</sub> - V <sub>O</sub> + V <sub>O</sub> - V <sub>OL</sub> V <sub>OH</sub>	13.4 - 13.4 - - 3.7	13.9 -13.9 14 -14.7	- -13.5 - -14.1 0.2 5.0	V
Common Mode Rejection (V <sub>in</sub> = +13.2 V to -15 V)	13	CMR	80	100	_	dB
Power Supply Rejection V <sub>CC</sub> /V <sub>EE</sub> = +15 V/ -15 V, +5.0 V/ -15 V, +15 V/ -5.0 V	14, 15	PSR	80	105	-	dB
Output Short Circuit Current (V <sub>ID</sub> = 1.0 V, Output to Ground) Source Sink	16	I <sub>SC</sub>	+25 -25	+37 -37	- -	mA
Power Supply Current Per Amplifier ( $V_O = 0 \text{ V}$ ) ( $V_{CC} = +15 \text{ V}$ , $V_{EE} = -15 \text{ V}$ ) $T_A = +25^{\circ}\text{C}$ $T_A = T_{low} \text{ to } T_{high}$ ( $V_{CC} = 5.0 \text{ V}$ , $V_{EE} = 0 \text{ V}$ ) $T_A = +25^{\circ}\text{C}$	17	Icc	- -	2.15 - -	2.75 3.0 2.75	mA

<sup>3.</sup> MC33272A, MC33274A  $T_{low} = -40^{\circ}C$   $T_{high} = +85^{\circ}C$  NCV33272A, NCV33274A  $T_{low} = -40^{\circ}C$   $T_{high} = +125^{\circ}C$ 

 $\textbf{AC ELECTRICAL CHARACTERISTICS} \ (V_{CC} = +15 \ V, \ V_{EE} = -15 \ V, \ T_{A} = 25^{\circ}C, \ unless \ otherwise \ noted.)$ 

Characteristics	Figure	Symbol	Min	Тур	Max	Unit
Slew Rate $(V_{in} = -10 \text{ V to } +10 \text{ V}, R_L = 2.0 \text{ k}\Omega, C_L = 100 \text{ pF}, A_V = +1.0 \text{ V})$	18, 33	SR	8.0	10	-	V/μs
Gain Bandwidth Product (f = 100 kHz)	19	GBW	17	24	-	MHz
AC Voltage Gain (R <sub>L</sub> = $2.0 \text{ k}\Omega$ , V <sub>O</sub> = $0 \text{ V}$ , f = $20 \text{ kHz}$ )	20, 21, 22	A <sub>VO</sub>	-	65	-	dB
Unity Gain Bandwidth (Open Loop)		BW	-	5.5	-	MHz
Gain Margin (R <sub>L</sub> = 2.0 k $\Omega$ , C <sub>L</sub> = 0 pF)	23, 24, 26	A <sub>m</sub>	-	12	_	dB
Phase Margin (R <sub>L</sub> = $2.0 \text{ k}\Omega$ , C <sub>L</sub> = $0 \text{ pF}$ )	23, 25, 26	φт	-	55	_	Deg
Channel Separation (f = 20 Hz to 20 kHz)	27	CS	-	-120	_	dB
Power Bandwidth ( $V_O = 20 V_{pp}$ , $R_L = 2.0 k\Omega$ , THD $\leq 1.0\%$ )		$BW_P$	-	160	_	kHz
Total Harmonic Distortion (R <sub>L</sub> = 2.0 k $\Omega$ , f = 20 Hz to 20 kHz, V <sub>O</sub> = 3.0 V <sub>rms</sub> , A <sub>V</sub> = +1.0)	28	THD	_	0.003	_	%
Open Loop Output Impedance (V <sub>O</sub> = 0 V, f = 6.0 MHz)	29	Z <sub>O</sub>	-	35	-	Ω
Differential Input Resistance (V <sub>CM</sub> = 0 V)		R <sub>in</sub>	-	16	-	ΜΩ
Differential Input Capacitance (V <sub>CM</sub> = 0 V)		C <sub>in</sub>	-	3.0	-	pF
Equivalent Input Noise Voltage (R <sub>S</sub> = 100 $\Omega$ , f = 1.0 kHz)	30	e <sub>n</sub>	-	18	=	nV/√Hz
Equivalent Input Noise Current (f = 1.0 kHz)	31	i <sub>n</sub>	-	0.5	-	pA/√Hz

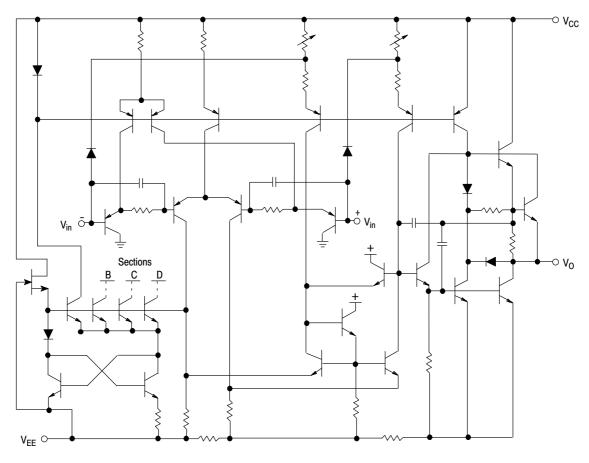


Figure 1. Equivalent Circuit Schematic (Each Amplifier)

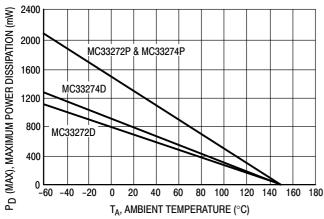


Figure 2. Maximum Power Dissipation versus Temperature

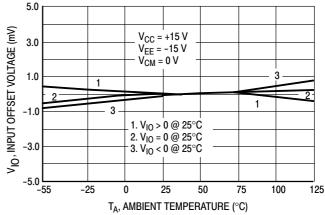


Figure 3. Input Offset Voltage versus Temperature for Typical Units

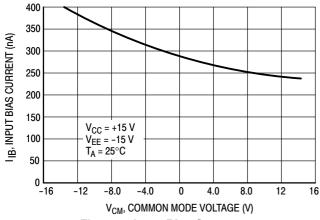


Figure 4. Input Bias Current versus Common Mode Voltage

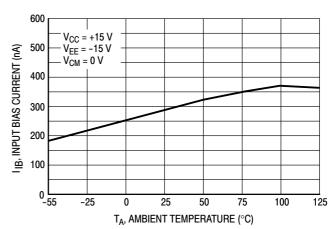


Figure 5. Input Bias Current versus Temperature

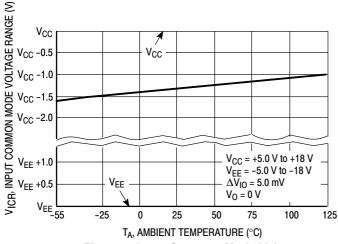


Figure 6. Input Common Mode Voltage Range versus Temperature

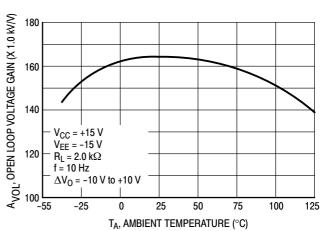


Figure 7. Open Loop Voltage Gain versus Temperature

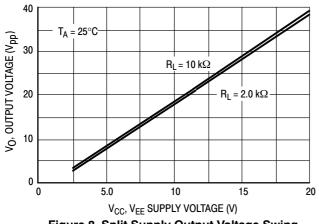


Figure 8. Split Supply Output Voltage Swing versus Supply Voltage

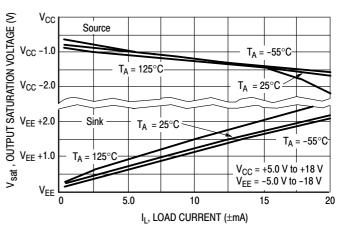


Figure 9. Split Supply Output Saturation Voltage versus Load Current

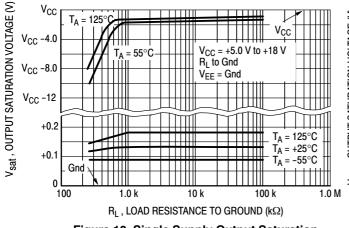


Figure 10. Single Supply Output Saturation Voltage versus Load Resistance to Ground

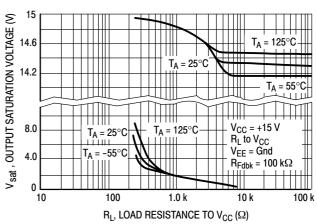


Figure 11. Single Supply Output Saturation Voltage versus Load Resistance to  $V_{CC}$ 

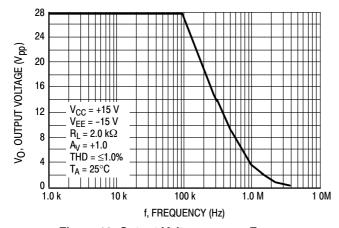


Figure 12. Output Voltage versus Frequency

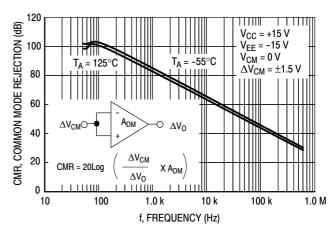


Figure 13. Common Mode Rejection versus Frequency

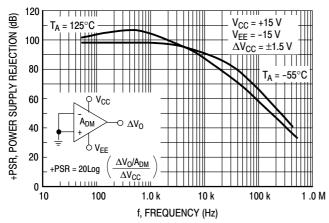


Figure 14. Positive Power Supply Rejection versus Frequency

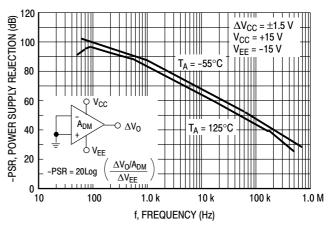


Figure 15. Negative Power Supply Rejection versus Frequency

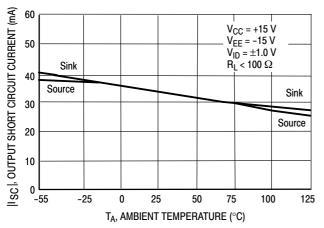


Figure 16. Output Short Circuit Current versus Temperature

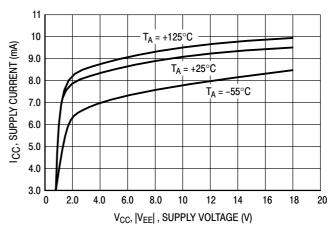


Figure 17. Supply Current versus Supply Voltage

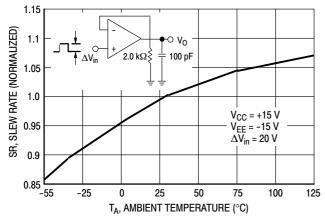


Figure 18. Normalized Slew Rate versus Temperature

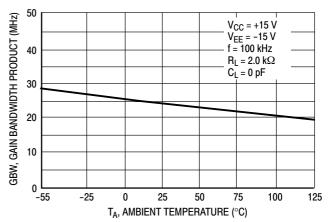


Figure 19. Gain Bandwidth Product versus Temperature

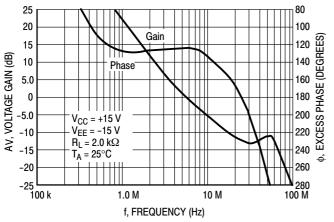


Figure 20. Voltage Gain and Phase versus Frequency

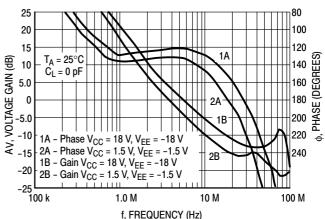


Figure 21. Gain and Phase versus Frequency

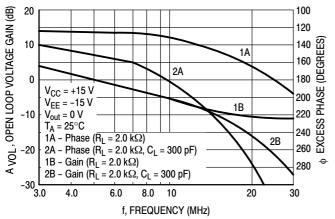


Figure 22. Open Loop Voltage Gain and Phase versus Frequency

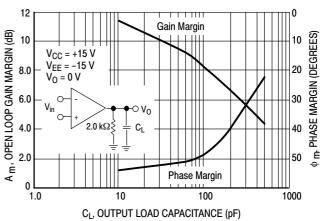


Figure 23. Open Loop Gain Margin and Phase Margin versus Output Load Capacitance

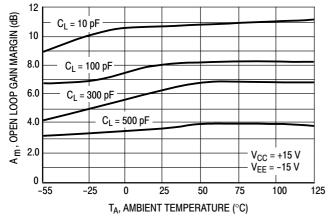


Figure 24. Open Loop Gain Margin versus Temperature

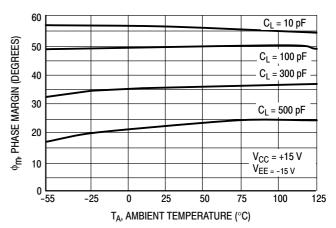


Figure 25. Phase Margin versus Temperature

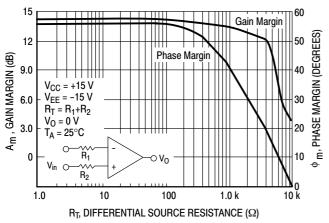


Figure 26. Phase Margin and Gain Margin versus Differential Source Resistance

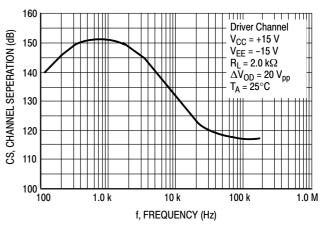


Figure 27. Channel Separation versus Frequency

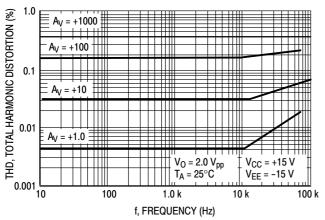


Figure 28. Total Harmonic Distortion versus Frequency

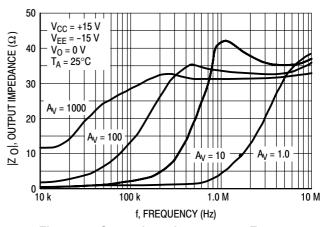


Figure 29. Output Impedance versus Frequency

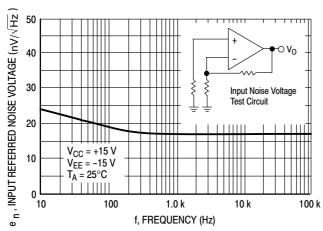


Figure 30. Input Referred Noise Voltage versus Frequency

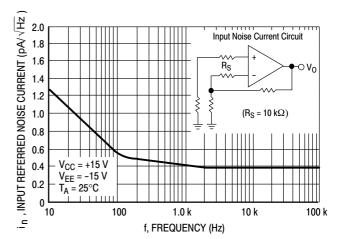


Figure 31. Input Referred Noise Current versus Frequency

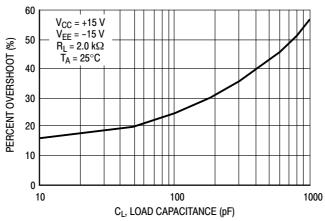


Figure 32. Percent Overshoot versus Load Capacitance

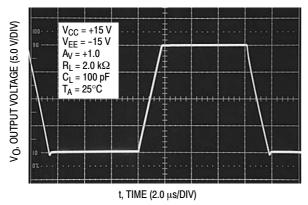


Figure 33. Non-inverting Amplifier Slew Rate for the MC33274

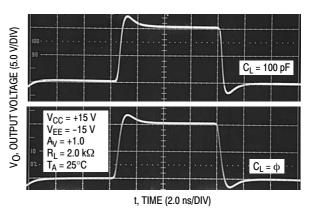


Figure 34. Non-inverting Amplifier Overshoot for the MC33274

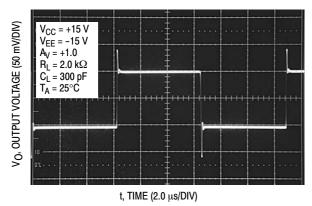


Figure 35. Small Signal Transient Response for MC33274

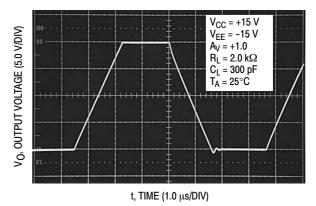


Figure 36. Large Signal Transient Response for MC33274

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC33272AD	SOIC-8	
MC33272ADG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33272ADR2	SOIC-8	
MC33272ADR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC33272AP	PDIP-8	
MC33272APG	PDIP-8 (Pb-Free)	50 Units / Rail
NCV33272ADR2*	SOIC-8	
NCV33272ADR2G*	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC33274AD	SOIC-14	
MC33274ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC33274ADR2	SOIC-14	
MC33274ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC33274ADTBR2G	TSSOP-14 (Pb-Free)	
MC33274AP	PDIP-14	
MC33274APG	PDIP-14 (Pb-Free)	25 Units / Rail
NCV33274AD*	SOIC-14	
NCV33274ADG*	SOIC-14 (Pb-Free)	55 Units / Rail
NCV33274ADR2*	SOIC-14	
NCV33274ADR2G*	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NCV33274ADTBR2G*	TSSOP-14 (Pb-Free)	

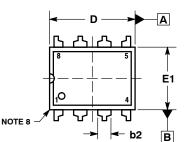
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

Capable.

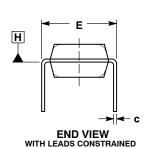


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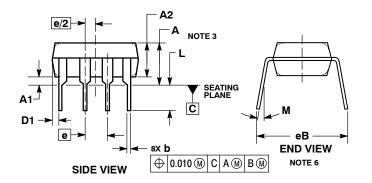
**DATE 22 APR 2015** 



**TOP VIEW** 



NOTE 5



STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN

5. GROUND 6. OUTPUT 7. AUXILIARY 8. V<sub>CC</sub>

#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
  DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
- 6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- LEADS UNCONSTRAINED.

  DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52 TYP	
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54 BSC	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

#### **GENERIC MARKING DIAGRAM\***



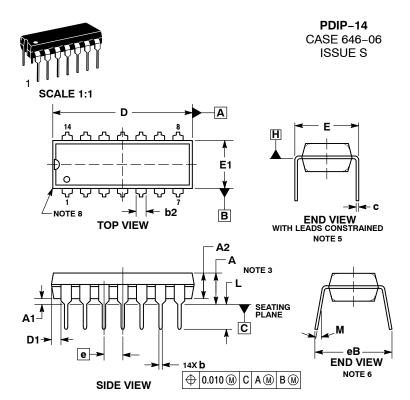
XXXX = Specific Device Code = Assembly Location WL = Wafer Lot

YY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	PDIP-8		PAGE 1 OF 1

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**DATE 22 APR 2015** 

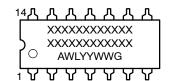
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
  3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
- NOT TO EXCEED 0.10 INCH.
  DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
- DIMENSION 6B IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
- DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.

  PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE
- CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54 BSC	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

# **STYLES ON PAGE 2**

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#### PDIP-14 CASE 646-06 ISSUE S

#### **DATE 22 APR 2015**

STYLE 1: PIN 1. COLLECTOR 2. BASE 3. EMITTER 4. NO CONNECTION 5. EMITTER 6. BASE 7. COLLECTOR 8. COLLECTOR 9. BASE 10. EMITTER 11. NO CONNECTION 12. EMITTER 13. BASE 14. COLLECTOR	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. DRAIN 2. SOURCE 3. GATE 4. NO CONNECTION 5. GATE 6. SOURCE 7. DRAIN 8. DRAIN 9. SOURCE 10. GATE 11. NO CONNECTION 12. GATE 13. SOURCE 14. DRAIN
STYLE 5: PIN 1. GATE 2. DRAIN 3. SOURCE 4. NO CONNECTION 5. SOURCE 6. DRAIN 7. GATE 8. GATE 9. DRAIN 10. SOURCE 11. NO CONNECTION 12. SOURCE 13. DRAIN 14. GATE	STYLE 6: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 7: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 8: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 9: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE	STYLE 10: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 12: PIN 1. COMMON CATHODE 2. COMMON ANODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. COMMON ANODE 7. COMMON CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. ANODE/CATHODE 14. ANODE/CATHODE 14. ANODE/CATHODE

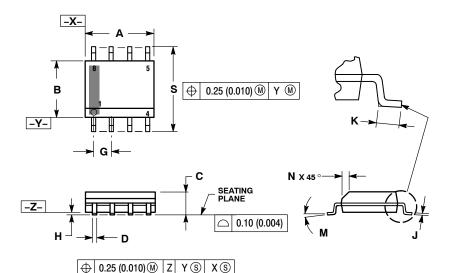
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SOIC-8 NB CASE 751-07 **ISSUE AK** 

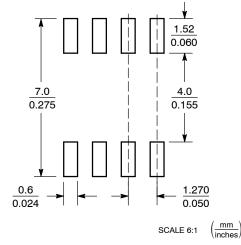
**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
7	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

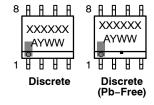
#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww

= Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

#### DATE 16 FEB 2011

STYLE 3: PIN 1. DRAIN, PIE #1 CTOR, #1 CTOR, #2 CTOR, #1 CTOR, #2 CTOR, #2 CTOR, #2 CTOR, #2 CTOR, #1	2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE  STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #1 Vd  STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN 8. TYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #1 4. ANODE 5. ANODE 6. ANODE 7. ANODE 7. ANODE 7. ANODE 7. ANODE 8. COMMON CATHODE 8. COMMON CATHODE 9. ANODE 7. ANODE 8. COMMON CATHODE 9. ANODE 9. ANO
E PIN 1. INPUT 2. EXTERNAL BY 3. THIRD STAGE 4. GROUND E 5. DRAIN 6. GATE 3 7. SECOND STAGE 8. FIRST STAGE STYLE 11: ID PIN 1. SOURCE 1 2. GATE 1 T 3. SOURCE 2 ID 4. GATE 2 ID 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 ID 8. DRAIN 1 ID	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 Vd 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN 8. TYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
ID PIN 1. SOURCE 1 2. GATE 1 T 3. SOURCE 2 ID 4. GATE 2 ID 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 ID 8. DRAIN 1 STYLE 15: RCE PIN 1. ANODE 1 E 2. ANODE 1 RCE 3. ANODE 1	PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
STYLE 15:  RCE PIN 1. ANODE 1 E 2. ANODE 1 RCE 3. ANODE 1	PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2
N 7. CATHODE, CON N 8. CATHODE, CON	MMON         5. COLLECTOR, DIE #2           MMON         6. COLLECTOR, DIE #2           MMON         7. COLLECTOR, DIE #1           MMON         8. COLLECTOR, DIE #1
STYLE 19: PIN 1. SOURCE 1 E 2. GATE 1 E 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 DE 7. DRAIN 1 DE 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 23: E1 PIN 1. LINE 1 IN DN CATHODE/VCC 2. COMMON ANC DN CATHODE/VCC 3. COMMON ANC E3 4. LINE 2 IN DN ANODE/GND 5. LINE 2 OUT E4 6. COMMON ANC E5 7. COMMON ANC DN ANODE/GND 8. LINE 1 OUT	ODE/GND 2. EMITTER ODE/GND 3. COLLECTOR/ANODE
STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V MON 6. VBULK 7. VBULK 8. VIN
1 1	
;	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ E 5. SOURCE E 6. SOURCE E 7. SOURCE 8. DRAIN

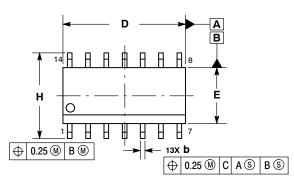
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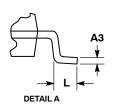
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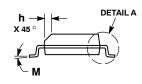


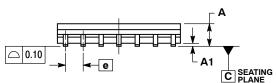
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 









#### 0.25 0.50 0.010 0.019 0.40 1.25 0.016 0.049

NOTES:
1. DIMENSIONING AND TOLERANCING PER

5. MAXIMUM MOLD PROTRUSION 0.15 PER

INCHES

MIN MAX

0.050 BSC

0.25 0.004 0.010

0.25 0.008 0.010

0.49 0.014

8.75 0.337 3.80 4.00 0.150 0.157

0.068

0.019

MILLIMETERS

MIN MAX

1.27 BSC

0.19

8.55

SIDE

Α

A1 0.10

АЗ

b 0.35

D E

e H h

ASME Y14.5M, 1994.
CONTROLLING DIMENSION: MILLIMETERS. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.



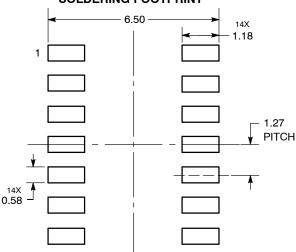
**GENERIC** 

XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year = Work Week WW G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

#### **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

#### **STYLES ON PAGE 2**

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

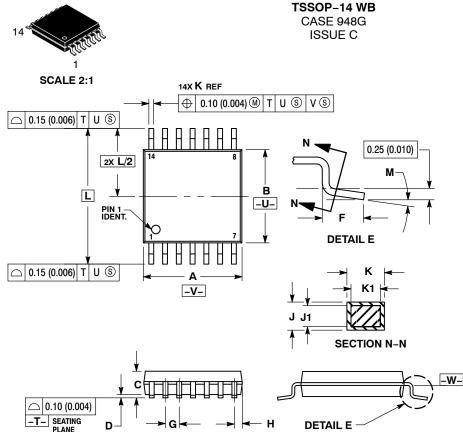
#### SOIC-14 CASE 751A-03 ISSUE L

#### DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

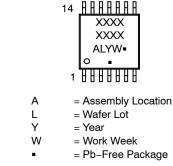
  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY.
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	
М	° o	8 °	0 °	8 °

#### **GENERIC MARKING DIAGRAM\***



(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

<b>—</b>	7.06
1	
	<del> </del>
	0.65
, <u> </u>	<b>→ →</b> • • • • • • • • • • • • • • • • • • •
14X	<del></del>
0.36 14X 1.26	DIMENSIONS: MILLIMETERS

**SOLDERING FOOTPRINT** 

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